



Hiroshima University  
21<sup>th</sup> Century COE Program

**Proceedings of  
First Hiroshima International Workshop on  
Nanoelectronics for  
Terra-Bit Information Processing**

**March 17, 2003**

**Hiroshima University  
Faculty Club**

# Preface

Recently, the Japanese Ministry of Education, Culture, Sports, Science and Technology has elected Hiroshima University as a Center of Excellence (COE) on "Nanoelectronics for Terra-Bit Information Processing" in its 21<sup>st</sup> Century COE Program. The scientific core of this COE is formed by the Research Center for Nanodevices and Systems (RCNS) and cooperating members from the Graduate School for Advanced Sciences of Matter.

The purpose of this workshop is to offer the forum for discussing future prospects of silicon nanoelectronics and nanodevice technologies with the experts in the related fields.

Our main goals are:

- \* Unification of silicon-based system, circuit, device-modeling and device-fabrication research
- \* Solution of the persistent 3-dimensional-integration problems by a wireless integration methodology
- \* Realization of integrated systems with high-level recognition and learning capabilities by innovative circuits and architectures

Our research fields and present research subjects are summarized as follows:

## I. Electronic circuits and system architecture

### I-1. High frequency analog circuits

Prof. A. Iwata & Assoc. Prof. M. Sasaki

### I-2. Associative-memory-based systems with recognition and learning capability

Prof. H. J. Mattausch & Assoc. Prof. T. Koide

### I-3. Processing system with highly cognitive level

Prof. A. Iwata

## II. Device Modeling

### II-1. Integration of electronic and optical devices

Prof. M. Miura-Mattausch & Res. Assoc. Dr. H. Ueno

### II-2. Three-dimensional SOI-MOS device integration

Prof. M. Miura-Mattausch & Res. Assoc. Dr. H. Ueno

## III. Nanodevices and Processes

### III-1. Fundamental miniaturization techniques for Si-MOS transistors

Assoc. Prof. K. Shibahara

### III-2. Three-dimensional ultra-small SOI-MOS transistors

Prof. H. Sunami & Prof. M. Miura-Mattausch

### III-3. Functional devices with nanostructure

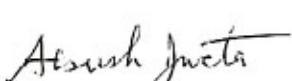
Prof. S. Miyazaki & Res. Assoc. H. Murakami

### III-4. Integration technologies for wireless interconnect systems

Prof. T. Kikkawa & Assoc. Prof. M. Sasaki

### III-5. Optoelectronic integrated systems using optical interconnection on a Si chip

Prof. S. Yokoyama & Assoc. Prof. A. Nakajima



Atsushi Iwata

Leader of the 21<sup>st</sup> Century COE program on  
Nanoelectronics of Tera-bit Information Processing

Director of the Research Center for Nanodevices and Systems

Hiroshima University

1-3-1 Kagamiyama, Higashi-Hiroshima 739-8530

Japan

E-mail: iwa@dsl.hiroshima-u.ac.jp

## CONTENTS

9:00	<b>Opening</b>	
	Address .....	1
	Univ. President Prof. Taizo Muta	
9:05	<b>Overview &amp; Keynote</b>	
	-Targets and research plan of 21st century COE- .....	2
	Profs. Atsushi Iwata, Hans Juergen Mattausch, Mitiko Miura-Mattausch and Hideo Sunami	
10:00	<b>(Invited) Industry-Academia Cooperation for Advanced Semiconductor Technology</b> .....	15
	Dr. Masataka Hirose (AIST, MIRAI)	
11:00	<b>(Invited) Strategic directions of semiconductor consortia and expectation to COE program</b> .....	30
	Dr. Toyoki Takemoto (STARC)	
13:30	<b>(Invited) Challenges and opportunities in the design of future systems on chip</b> .....	44
	Prof. Tobias G. Noll (Aachen Univ. of Technol.)	
14:30	<b>(Invited) The impact of nm CMOS technology on wireless circuit and system</b> .....	72
	Prof. Kwyro Lee (KAIST)	
15:30	<b>(Invited) Silicon microphotonics</b>	
	- Photons meet LSIs .....	92
	Prof. Kazumi Wada (MIT)	
16:30	<b>HiSIM: Present status and future perspective</b> .....	102
	Prof. Mitiko Miura-Mattausch	
17:00	<b>Poster Presentations by COE Members</b>	
P-1	<b>3dimensional global/local wireless interconnection for hierarchical processing systems</b> .....	111

	Atsushi Iwata and Mamoru Sasaki	
P-2	<b>Image segmentation/extraction using nonlinear pixel-parallel networks and thier VLSI implementation</b>	117
	Hiroshi Ando, Takashi Morie and Atsushi Iwata	
P-3	<b>An analog VLSI chip calculating high-precision spatial and temporal derivatives of the vertebrate retina</b>	121
	Seiji Kameda and Tetsuya Yagi	
P-4	<b>Associative memory -based systems with recognition and learning capability</b>	123
	Tetsushi Koide and Hans Juergen Mattausch	
P-5	<b>Fully-parallel associative memory for fast pattern matching</b>	129
	Yuji Yano, Minoru Honda, Masahiro Misokami, Tetsushi Koide and Hans Juergen Mattausch	
P-6	<b>Digital-CMOS-based real-time color-motion picture segmentation</b>	134
	Takashi Morimoto, Youmei Harada, Tetsushi Koide and Hans Juergen Mattausch	
P-7	<b>HiSIM-SOI: The first surface-potential-based fully-depleted SOI-MOSFET model for circuit simulation development and future tasks</b>	139
	Daisuke Kitamaru, Yasuhito Uetsuji and Mitiko Miura-Mattausch	
P-8	<b>Electron transport in MOSFET's inversion layer under high electric field</b>	145
	Masayasu Tanaka, Hiroaki Ueno, Osamu Matsushima and Mitiko Miura-Mattausch	
P-9	<b>Optical interconnection technology at RCNS Hiroshima University</b>	151
	Shin Yokoyama, Kazutaka Umeda and Anri Nakajima	
P-10	<b>Silicon integrated antennas for wireless interconnects</b>	158
	Takamaro Kikkawa, ABM Harun Rashid and Shinji Watanabe	

P-11	<b>Photosensitive low-dielectric-constant films for ULSI interconnects</b>	168
	Shin-ichiro Kuroki and Takamaro Kikkawa	
P-12	<b>Proposal of three-dimensional MOS transistors with high drivability for area-conscious applications</b>	174
	Hideo Sunami and Akira Katakami	
P-13	<b>Technology and application of photonic crystal</b>	176
	Anri Nakajima, Masaru Wake and Shin Yokoyama	
P-14	<b>Atomic-layer deposition of ZrO<sub>2</sub> gate dielectrics with a Si nitride barrier layer</b>	179
	Hiroyuki Ishii and Anri Nakajima	
P-15	<b>Workfunction tuning technique for dual-gate CMOS with single metal gate</b>	182
	Kentaro Shibarara	
P-16	<b>Self-assembling of Si quantum dots and their application to memory devices</b>	188
	Seiichi Miyazaki	
P-17	<b>Multiple-step electron charging in Si quantum-dot floating gate MOS memories</b>	195
	Mitsuhisa Ikeda, Yusuke Shimizu, Hideki Murakami and Seiichi Miyazaki	
P-18	<b>Electronic charged state of single Si quantum dots with and without Ge core as detected by AFM/Kelvin probe technique</b>	200
	Yudi Darma, Kohei Takeuchi, Hideki Murakami and Seiichi Miyazaki	

18:30 **Closing Remarks**

Prof. Hideo Sunami